Vishay Semiconductors



Hyperfast Rectifier, 2 x 4 A FRED Pt®



LINKS TO ADDITIONAL RESOURCES



PRIMARY CHARACTERISTICS						
I _{F(AV)}	2 x 4 A					
V _R	100 V					
V _F at I _F	0.71 V					
t _{rr} (typ.)	16 ns					
T _J max.	175 °C					
Package	SlimDPAK (TO-252AE)					
Circuit configuration	Common cathode					

FEATURES

- Hyperfast recovery time
- 175 °C max. operating junction temperature
- \bullet Low forward voltage drop reduced Q_{rr} and soft recovery
- Low leakage current
- Very low profile typical height of 1.3 mm
- Polyimide passivation for high reliability
- standardIdeal for automated placement
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- AEC-Q101 qualified, meets JESD 201 class 2 whisker test
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION / APPLICATIONS

State of the art hyper fast recovery rectifiers designed with optimized performance of forward voltage drop, hyperfast recovery time, and soft recovery.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in PFC boost stage in the AC/DC section of SMPS inverters or as freewheeling diodes. Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

MECHANICAL DATA

Case: SlimDPAK (TO-252AE)

Molding compound meets UL 94 V-0 flammability rating Halogen-free, RoHS-compliant

Terminals: matte tin plated leads, solderable per J-STD-002

ABSOLUTE MAXIMUM RATINGS						
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Peak repetitive reverse voltage		V _{RRM}		100	V	
Average rectified forward	per leg	I	T _C = 167 °C	4		
current	per device	IF(AV)	$1_{\rm C} = 107$ C	8	А	
Non-repetitive peak surge current per leg		I _{FSM}	$T_J = 25 \ ^{\circ}C$, 10 ms sine pulse wave	100		
Operating junction and storage temperatures		T _J , T _{Stg}		-55 to +175	°C	

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Breakdown voltage, blocking voltage	V _{BR} , V _R	I _R = 100 μA	100	-	-		
		$I_F = 4 A$	-	0.88	1.0		
Forward valtage per lag	V _F	I _F = 8 A	-	0.97	1.14	V	
Forward voltage per leg		٧F	I _F = 4 A, T _J = 150 °C	-	0.71	0.80	
		I _F = 8 A, T _J = 150 °C	-	0.8	1.0		
		$V_{R} = V_{R}$ rated	-	-	4		
Reverse leakage current per leg	I _R	$T_J = 125 \text{ °C}, V_R = V_R \text{ rated}$	-	-	40	μA	
		$T_J = 150 \text{ °C}, V_R = V_R \text{ rated}$	-	-	80		
Junction capacitance per leg	C _T	V _R = 100 V	-	17	-	pF	

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RoHS

COMPLIANT

HALOGEN

FREE



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DYNAMIC RECOVERY CHARACTERISTICS (T_J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS	
		I _F = 1 A, dI _F /dt = 100 A/µs, V _R = 30 V		-	16	-	
Reverse recovery time	+	I _F = 0.5 A, I _R = 1 A	I _F = 0.5 A, I _R = 1 A, I _{RR} = 0.25 A		-	25	
neverse recovery time	t _{rr}	T _J = 25 °C		-	20	-	A ns
		T _J = 125 °C	I _F = 4 A dI _F /dt = 200 A/μs V _B = 160 V	-	30	-	
Peak recovery current	I _{RRM}	T _J = 25 °C		-	2.5	-	
Feat recovery current		T _J = 125 °C		-	4	-	
Reverse recovery charge C	Q _{rr}	T _J = 25 °C]	-	25	-	nC
		T _J = 125 °C		-	60	-	

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Maximum junction and storage temperature range	T _J , T _{Stg}		-55	-	175	°C	
Thermal resistance, junction to ambient per diode	R _{thJA} ⁽¹⁾⁽²⁾		-	73	90	°C/W	
Thermal resistance, junction to mount per diode	R _{thJM} ⁽³⁾		-	2.1	2.5	°C/W	
Weight			-	0.20	-	g	
Marking device		Case style SlimDPAK (TO-252AE)		8CV	'H01		

Notes

 $^{(1)}$ The heat generated must be less than thermal conductivity from junction to ambient; $dP_D/dT_J < 1 R_{thJA}$

 $^{(2)}$ Free air, mounted or recommended copper pad area; thermal resistance R_{thJA} - junction to ambient

⁽³⁾ Mounted on infinite heatsink

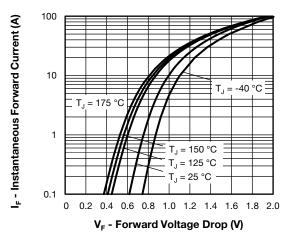


Fig. 1 - Typical Forward Voltage Drop Characteristics

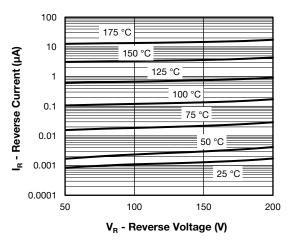
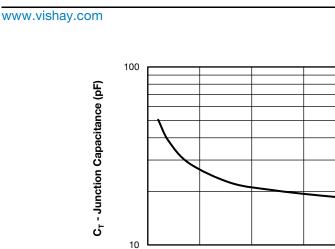


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

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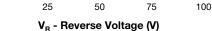


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

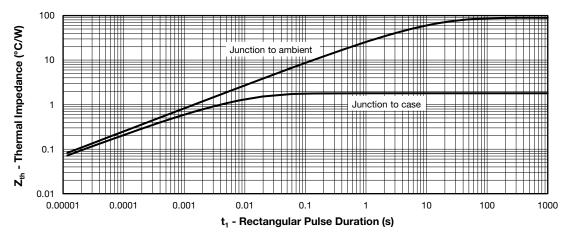


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

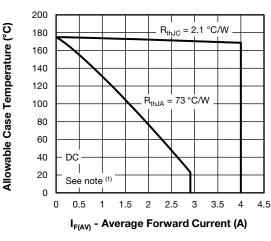


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

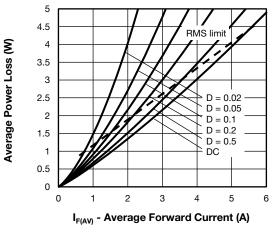


Fig. 6 - Forward Power Loss Characteristics

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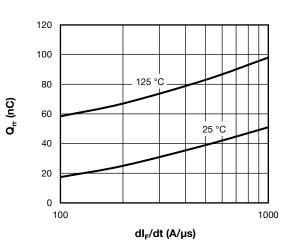
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Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt

Note

- ⁽¹⁾ Formula used: $T_C = T_J (Pd + Pd_{REV}) \times R_{thJC}$;
- $\begin{array}{l} \mbox{Pd} = \mbox{forward power loss} = \mbox{I}_{F(AV)} \times \mbox{V}_{FM} \mbox{ at } (\mbox{I}_{F(AV)}/\mbox{D}) \mbox{ (see fig. 6);} \\ \mbox{Pd}_{REV} = \mbox{inverse power loss} = \mbox{V}_{R1} \times \mbox{I}_{R} \mbox{ (1 D); I}_{R} \mbox{ at } \mbox{V}_{R1} = \mbox{rated } \mbox{V}_{R} \end{array}$



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Fig. 8 - Typical Stored Charge vs. dl_F/dt

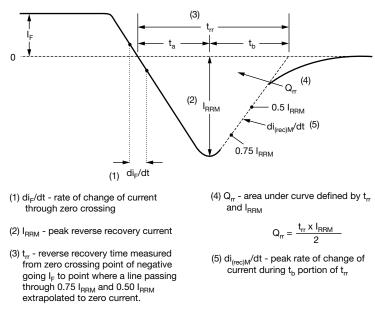


Fig. 9 - Reverse Recovery Waveform and Definitions

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Device code	VS-	8	С	v	н	01	н	М3	
		2	3	4	5	6	7	8	
	1 2		-	niconduo ng (8 = 3	•	oduct			
	3	- Circ	uit conf	iguratior	י:				
	4		SlimDP	n catho AK	ae				
	5		cess typ hyperfa	e, st recov	ery				
	6		0	de (01 =	,				
	7.			101 qua					
	8	- M3	= halog	en-tree,	RoHS-0	complia	nt, and	terminat	tions lead (Pt

ORDERING INFORMATION (Example)							
PREFERRED P/N	P/N QUANTITY PER REEL MINIMUM ORDER QUANTITY PACKAGING DESCRIPTION						
VS-8CVH01HM3/I	4500	4500	13"diameter plastic tape and reel				

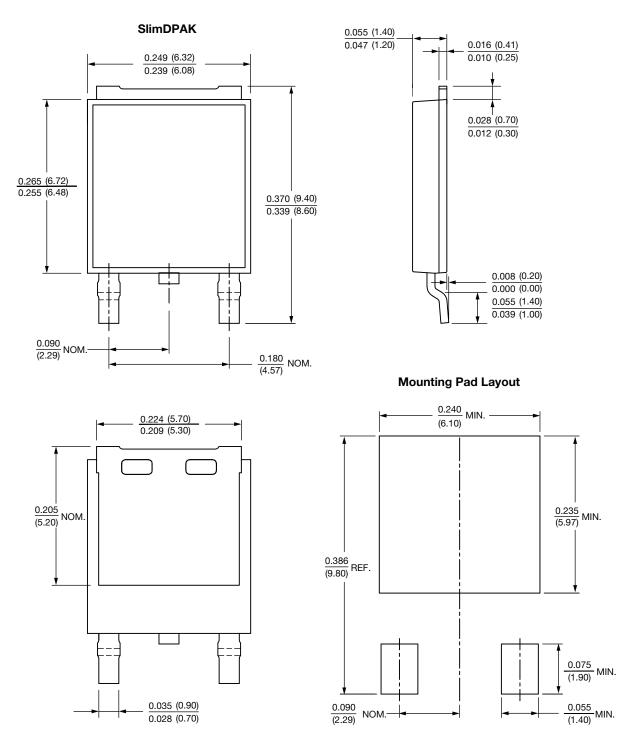
LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?96081				
Part marking information	www.vishay.com/doc?96085				
Packaging information	www.vishay.com/doc?88869				
SPICE model	www.vishay.com/doc?97122				





SlimDPAK

DIMENSIONS in inches (millimeters)





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